



**THE DATASHEET OF
ZVN3306A**



ZVN3306A

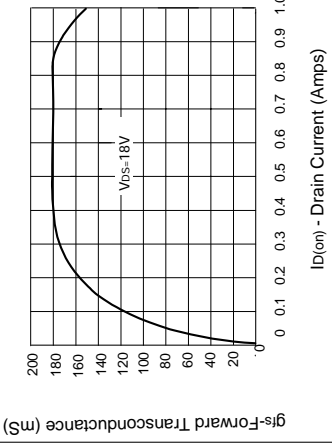
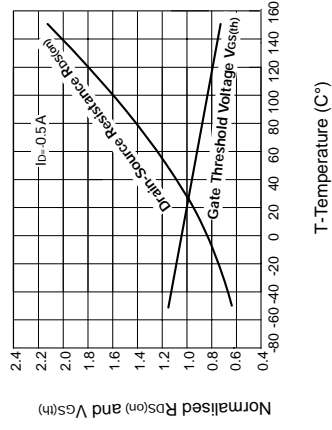
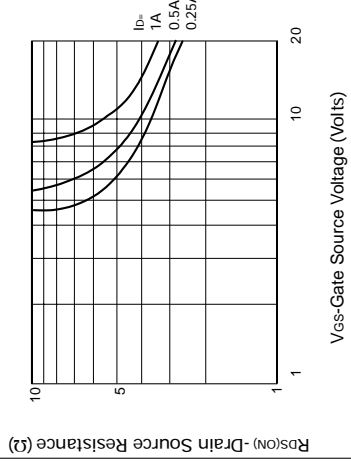
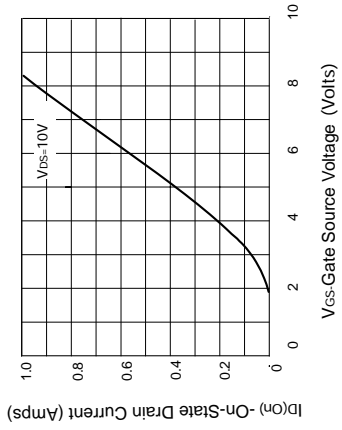
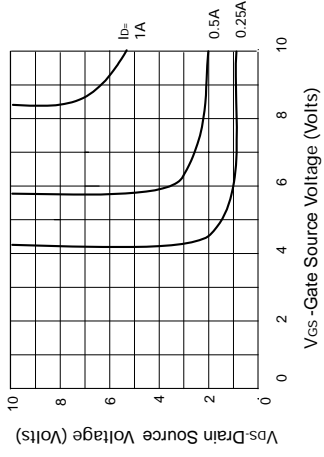
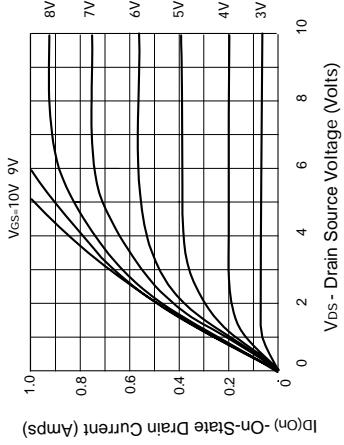
N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 – MARCH 94

FEATURES

- * 60 Volt V_{DS}
- * $R_{DS(on)}$ = 5 Ω

TYPICAL CHARACTERISTICS



ABSOLUTE MAXIMUM RATINGS

PARAMETER
Drain-Source Voltage
Continuous Drain Current at $T_{amb}=25^{\circ}C$
Pulsed Drain Current
Gate-Source Voltage
Power Dissipation at $T_{amb}=25^{\circ}C$
Operating and Storage Temperature Range

ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL
Drain-Source Breakdown Voltage	BV_{DSS}
Gate-Source Threshold Voltage	$V_{GS(th)}$
Gate-Body Leakage	I_{GSS}
Zero Gate Voltage Drain Current	I_{DSS}
On-State Drain Current(1)	$I_{D(on)}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$
Forward Transconductance(1)(2)	g_{fs}
Input Capacitance (2)	C_{iss}
Common Source Output Capacitance (2)	C_{oss}
Reverse Transfer Capacitance (2)	C_{rss}
Turn-On Delay Time (2)(3)	$t_{d(on)}$
Rise Time (2)(3)	t_r
Turn-Off Delay Time (2)(3)	$t_{d(off)}$
Fall Time (2)(3)	t_f

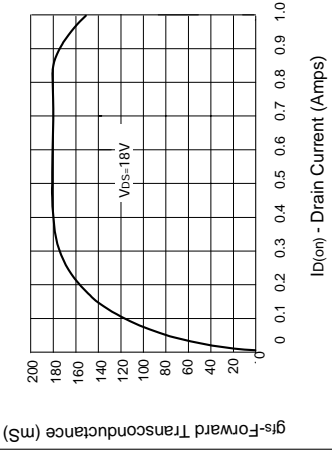
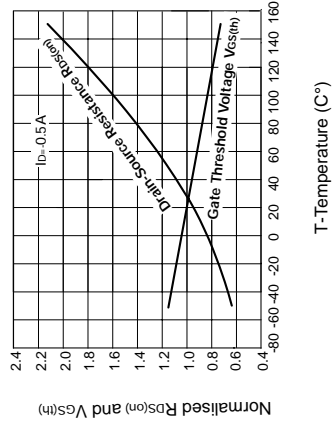
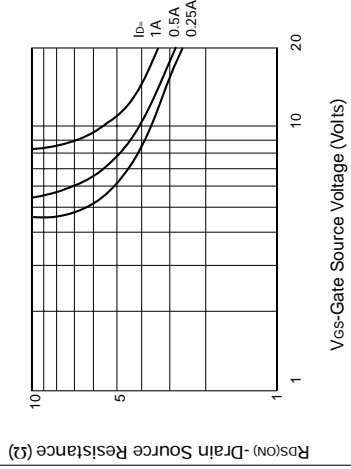
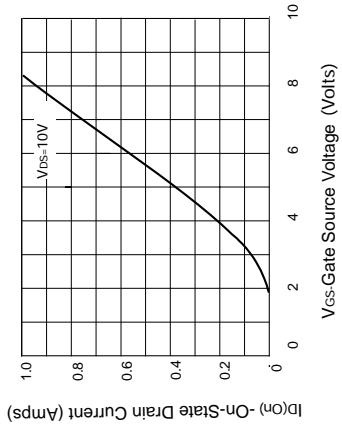
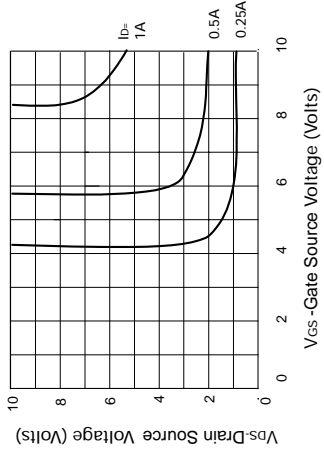
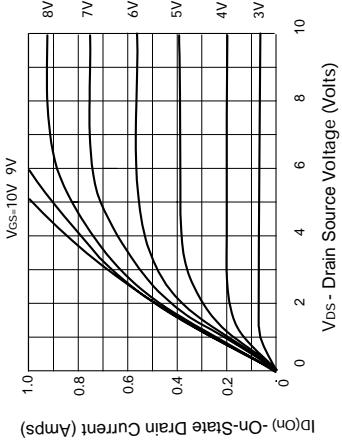
(1) Measured under pulsed conditions. $W_{rrm} = 100\mu s$, $D = 10\%$

3-376

2) Sample test.

ZVN3306A

TYPICAL CHARACTERISTICS



N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 - MARCH 94

FEATURES

- * 60 Volt V_{DS}
- * $R_{DS(on)}$ = 5 Ω

ABSOLUTE MAXIMUM RATINGS

PARAMETER
Drain-Source Voltage
Continuous Drain Current at $T_{amb}=25^{\circ}C$
Pulsed Drain Current
Gate-Source Voltage
Power Dissipation at $T_{amb}=25^{\circ}C$
Operating and Storage Temperature Range

ELECTRICAL CHARACTERISTICS

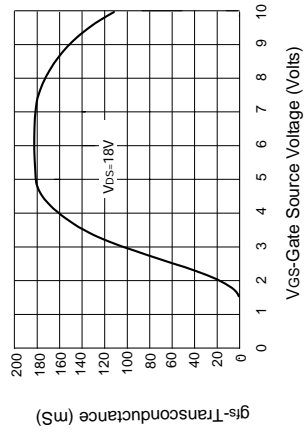
PARAMETER	SYMBOL
Drain-Source Breakdown Voltage	BV_{DSS}
Gate-Source Threshold Voltage	$V_{GS(th)}$
Gate-Body Leakage	I_{GSS}
Zero Gate Voltage Drain Current	I_{DSS}
On-State Drain Current(1)	$I_{D(on)}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$
Forward Transconductance(1)(2)	g_{fs}
Input Capacitance (2)	C_{iss}
Common Source Output Capacitance (2)	C_{oss}
Reverse Transfer Capacitance (2)	C_{rss}
Turn-On Delay Time (2)(3)	$t_{d(on)}$
Rise Time (2)(3)	t_r
Turn-Off Delay Time (2)(3)	$t_{d(off)}$
Fall Time (2)(3)	t_f

(1) Measured under pulsed conditions. $W_{eff} = 100\mu m$

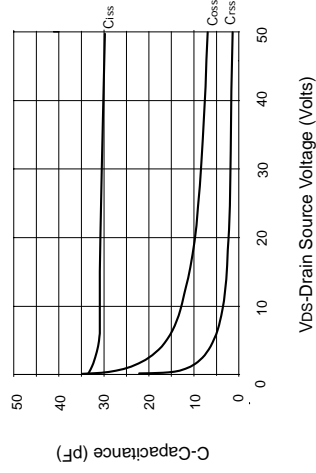
(2) Sample test.

ZVN3306A

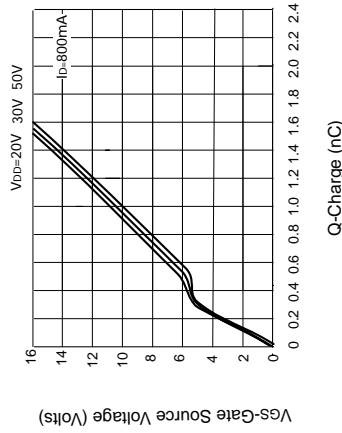
TYPICAL CHARACTERISTICS



Transconductance v gate-source voltage



Capacitance v drain-source voltage



Gate charge v gate-source voltage

Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

- ⊖ [View ZVN3306A on WIN SOURCE](#)
- ⊖ [Diodes Incorporated Information](#)

Optimize Your Supply Chain with WIN SOURCE Solutions

- ✓ Global Sourcing Solution
- ✓ Obsolete Management
- ✓ Cost Control Management
- ✓ Shortage Management
- ✓ Alternative Solution
- ✓ Excess Inventory Management